

ISL9V2540S3S

EcoSPARK™ N-Channel Ignition IGBT

250mJ, 400V

Features

- SCIS Energy = 250mJ at $T_J = 25^\circ\text{C}$
- Logic Level Gate Drive

Applications

- Automotive Ignition Coil Driver Circuits
- Coil - On Plug Applications

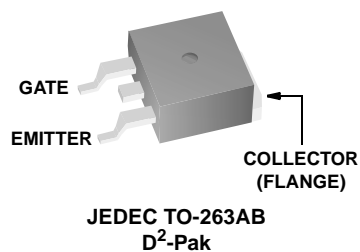
General Description

The ISL9V2540S3S is a next generation ignition IGBT that offers outstanding SCIS capability in the industry standard D²-Pak (TO-263) plastic package. This device is intended for use in automotive ignition circuits, specifically as a coil driver. Internal diodes provide voltage clamping without the need for external components.

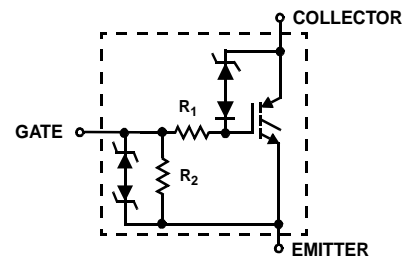
EcoSPARK™ devices can be custom made to specific clamp voltages. Contact your nearest Fairchild sales office for more information.

ISL9V2540S3S N-Channel Ignition IGBT

Package



Symbol



Device Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Ratings | Units |
|---------------|---|------------|---------------------|
| BV_{CER} | Collector to Emitter Breakdown Voltage ($I_C = 1\text{ mA}$) | 430 | V |
| BV_{ECS} | Emitter to Collector Voltage - Reverse Battery Condition ($I_C = 10\text{ mA}$) | 24 | V |
| E_{SCIS25} | At Starting $T_J = 25^\circ\text{C}$, $I_{SCIS} = 12.9\text{A}$, $L = 3.0\text{mH}$ | 250 | mJ |
| $E_{SCIS150}$ | At Starting $T_J = 150^\circ\text{C}$, $I_{SCIS} = 10\text{A}$, $L = 3.0\text{mH}$ | 150 | mJ |
| I_{C25} | Collector Current Continuous, At $T_C = 25^\circ\text{C}$, See Fig 9 | 15.5 | A |
| I_{C110} | Collector Current Continuous, At $T_C = 110^\circ\text{C}$, See Fig 9 | 15.3 | A |
| V_{GEM} | Gate to Emitter Voltage Continuous | ± 10 | V |
| P_D | Power Dissipation Total $T_C = 25^\circ\text{C}$ | 166.7 | W |
| | Power Dissipation Derating $T_C > 25^\circ\text{C}$ | 1.11 | W/ $^\circ\text{C}$ |
| T_J | Operating Junction Temperature Range | -40 to 175 | $^\circ\text{C}$ |
| T_{STG} | Storage Junction Temperature Range | -40 to 175 | $^\circ\text{C}$ |
| T_L | Max Lead Temp for Soldering (Leads at 1.6mm from Case for 10s) | 300 | $^\circ\text{C}$ |
| T_{pkg} | Max Lead Temp for Soldering (Package Body for 10s) | 260 | $^\circ\text{C}$ |
| ESD | Electrostatic Discharge Voltage at 100pF, 1500 Ω (HBM) | 4 | kV |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|---------------|----------|-----------|------------|-----------|
| V2540S | ISL9V2540S3ST | TO-263AB | 330mm | 24mm | 800 units |
| V2540S | ISL9V2540S3S | TO-263AB | Tube | N/A | 50 units |

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

Off State Characteristics

| | | | | | | | |
|------------|--|--|---------------------------|----------|-----|----------|---------------|
| BV_{CER} | Collector to Emitter Breakdown Voltage | $I_C = 2\text{mA}$, $V_{GE} = 0$, $R_G = 1\text{K}\Omega$, See Fig. 15 $T_J = -40$ to 150°C | 370 | 400 | 430 | V | |
| BV_{CES} | Collector to Emitter Breakdown Voltage | $I_C = 10\text{mA}$, $V_{GE} = 0$, $R_G = 0$, See Fig. 15 $T_J = -40$ to 150°C | 390 | 420 | 450 | V | |
| BV_{ECS} | Emitter to Collector Breakdown Voltage | $I_C = -75\text{mA}$, $V_{GE} = 0\text{V}$, $T_C = 25^\circ\text{C}$ | 30 | - | - | V | |
| BV_{GES} | Gate to Emitter Breakdown Voltage | $I_{GES} = \pm 2\text{mA}$ | ± 12 | ± 14 | - | V | |
| I_{CER} | Collector to Emitter Leakage Current | $V_{CER} = 250\text{V}$, $R_G = 1\text{K}\Omega$, See Fig. 11 | $T_C = 25^\circ\text{C}$ | - | - | 25 | μA |
| | | | $T_C = 150^\circ\text{C}$ | - | - | 1 | mA |
| I_{ECS} | Emitter to Collector Leakage Current | $V_{EC} = 24\text{V}$, See Fig. 11 | $T_C = 25^\circ\text{C}$ | - | - | 1 | mA |
| | | | $T_C = 150^\circ\text{C}$ | - | - | 40 | mA |
| R_1 | Series Gate Resistance | | - | 70 | - | Ω | |
| R_2 | Gate to Emitter Resistance | | 10K | - | 26K | Ω | |

On State Characteristics

| | | | | | | | |
|---------------|---|--|--|---|------|-----|---|
| $V_{CE(SAT)}$ | Collector to Emitter Saturation Voltage | $I_C = 6\text{A}$, $V_{GE} = 4\text{V}$ | $T_C = 25^\circ\text{C}$, See Fig. 3 | - | 1.37 | 1.8 | V |
| $V_{CE(SAT)}$ | Collector to Emitter Saturation Voltage | $I_C = 10\text{A}$, $V_{GE} = 4.5\text{V}$ | $T_C = 150^\circ\text{C}$ See Fig. 4 | - | 1.77 | 2.2 | V |

Dynamic Characteristics

| | | | | | | | |
|--------------|-----------------------------------|--|---------------------|------|---|-----|---|
| $Q_{G(ON)}$ | Gate Charge | $I_C = 10A, V_{CE} = 12V,$ $V_{GE} = 5V, \text{ See Fig. 14}$ | - | 15.1 | - | nC | |
| $V_{GE(TH)}$ | Gate to Emitter Threshold Voltage | $I_C = 1.0mA,$ $V_{CE} = V_{GE},$ See Fig. 10 | $T_C = 25^\circ C$ | 1.3 | - | 2.2 | V |
| | | | $T_C = 150^\circ C$ | 0.75 | - | 1.8 | V |
| V_{GEP} | Gate to Emitter Plateau Voltage | $I_C = 10A,$ $V_{CE} = 12V$ | - | 3.1 | - | V | |

Switching Characteristics

| | | | | | | |
|---------------|---------------------------------------|---|---|------|-----|---------|
| $t_{d(ON)R}$ | Current Turn-On Delay Time-Resistive | $V_{CE} = 14V, R_L = 1\Omega,$ $V_{GE} = 5V, R_G = 1K\Omega,$ $T_J = 25^\circ C$ | - | 0.61 | - | μs |
| t_{riseR} | Current Rise Time-Resistive | | - | 2.17 | - | μs |
| $t_{d(OFF)L}$ | Current Turn-Off Delay Time-Inductive | $V_{CE} = 300V, L = 500\mu H,$ $V_{GE} = 5V, R_G = 1K\Omega,$ $T_J = 25^\circ C, \text{ See Fig. 12}$ | - | 3.64 | - | μs |
| t_{fL} | Current Fall Time-Inductive | | - | 2.36 | - | μs |
| SCIS | Self Clamped Inductive Switching | $T_J = 25^\circ C, L = 3.0mH,$ $R_G = 1K\Omega, V_{GE} = 5V, \text{ See}$ Fig. 1 \& 2 | - | - | 250 | mJ |

Thermal Characteristics

| | | | | | | |
|-----------------|----------------------------------|--------|---|---|-----|--------------|
| $R_{\theta JC}$ | Thermal Resistance Junction-Case | TO-263 | - | - | 0.9 | $^\circ C/W$ |
|-----------------|----------------------------------|--------|---|---|-----|--------------|

Typical Performance Curves

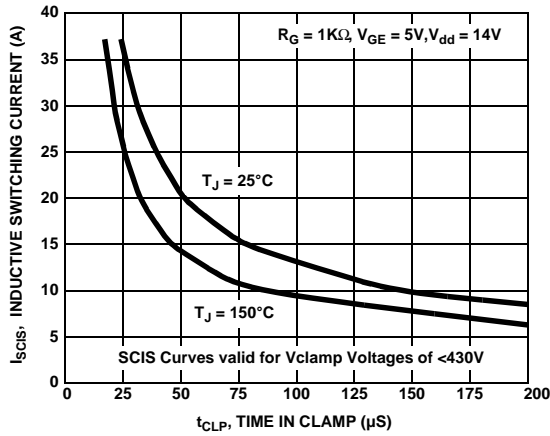


Figure 1. Self Clamped Inductive Switching Current vs Time in Clamp

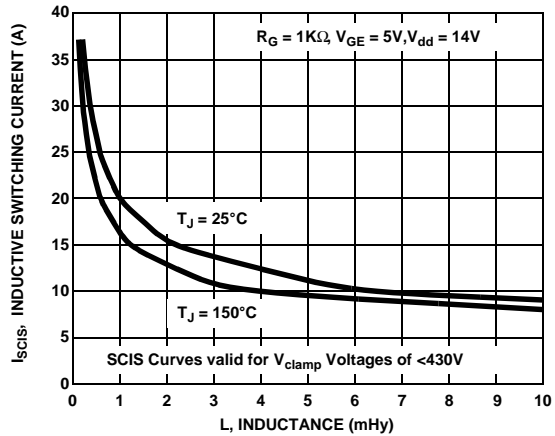


Figure 2. Self Clamped Inductive Switching Current vs Inductance

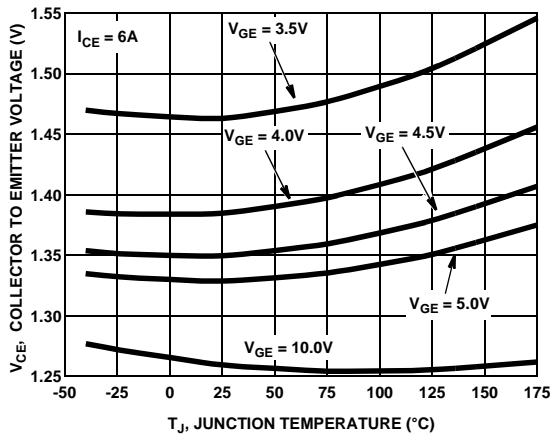


Figure 3. Collector to Emitter On-State Voltage vs Junction Temperature

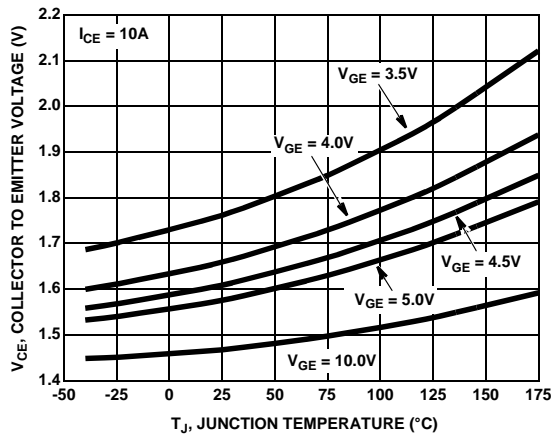


Figure 4. Collector to Emitter On-State Voltage vs Junction Temperature

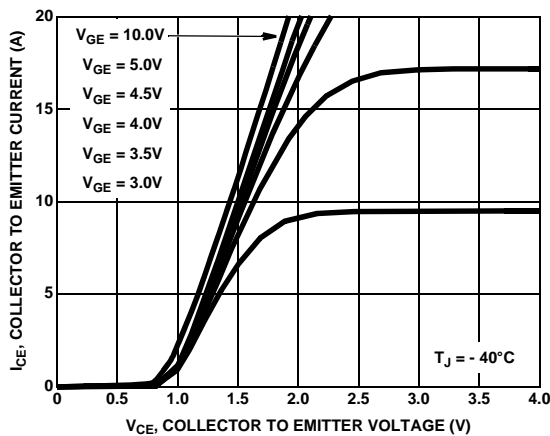


Figure 5. Collector to Emitter On-State Voltage vs Collector Current

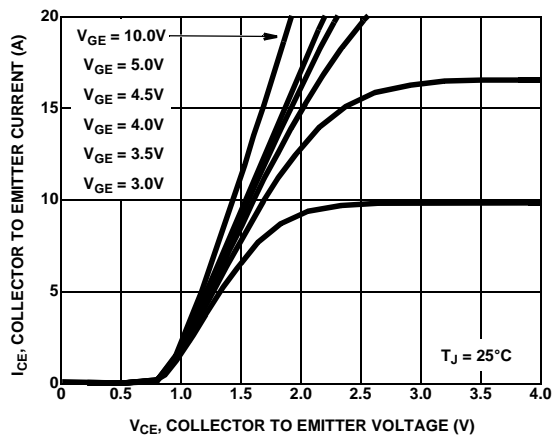


Figure 6. Collector to Emitter On-State Voltage vs Collector Current

Typical Performance Curves (Continued)

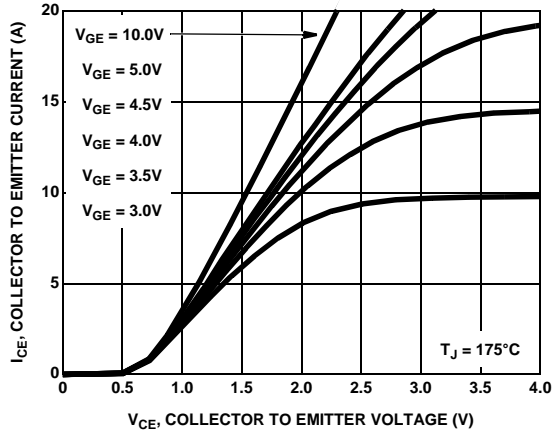


Figure 7. Collector to Emitter On-State Voltage vs Collector Current

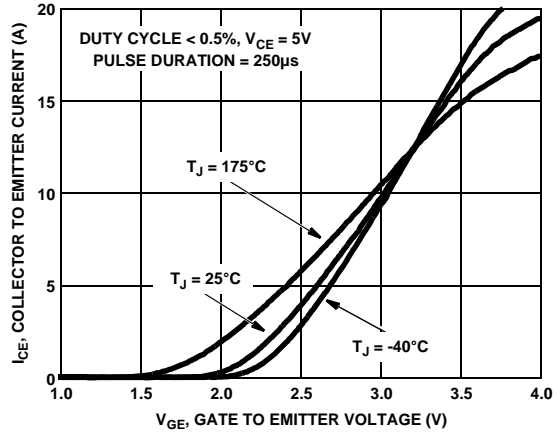


Figure 8. Transfer Characteristics

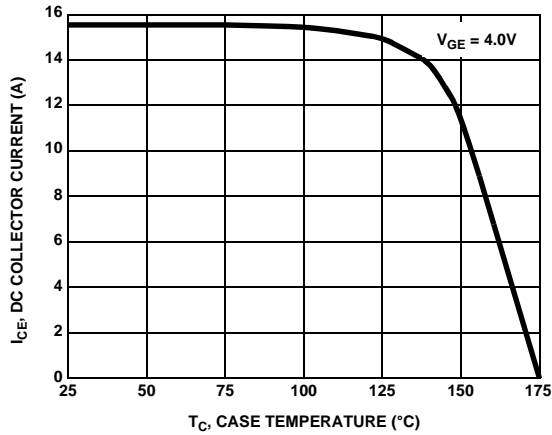


Figure 9. DC Collector Current vs Case Temperature

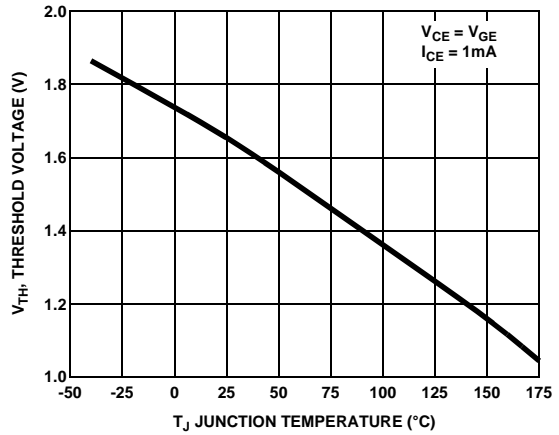


Figure 10. Threshold Voltage vs Junction Temperature

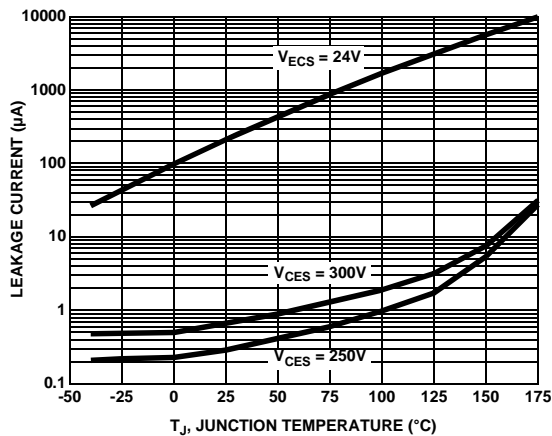


Figure 11. Leakage Current vs Junction Temperature

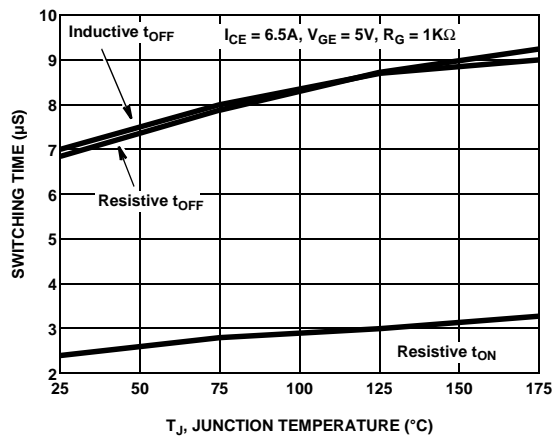


Figure 12. Switching Time vs Junction Temperature

Typical Performance Curves (Continued)

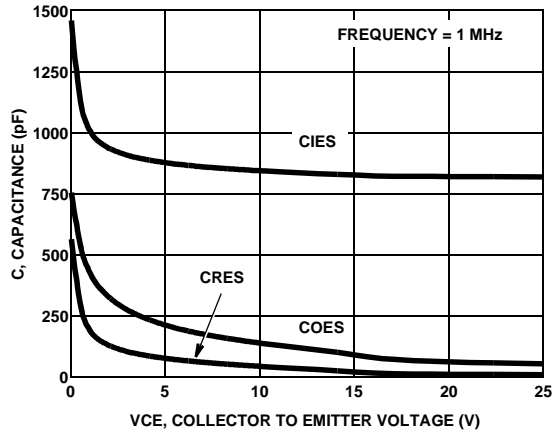


Figure 13. Capacitance vs Collector to Emitter Voltage

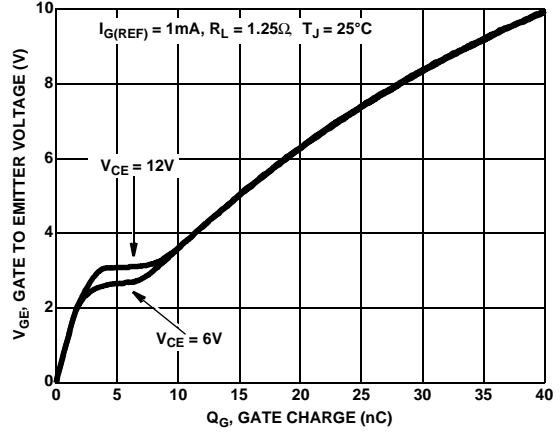


Figure 14. Gate Charge

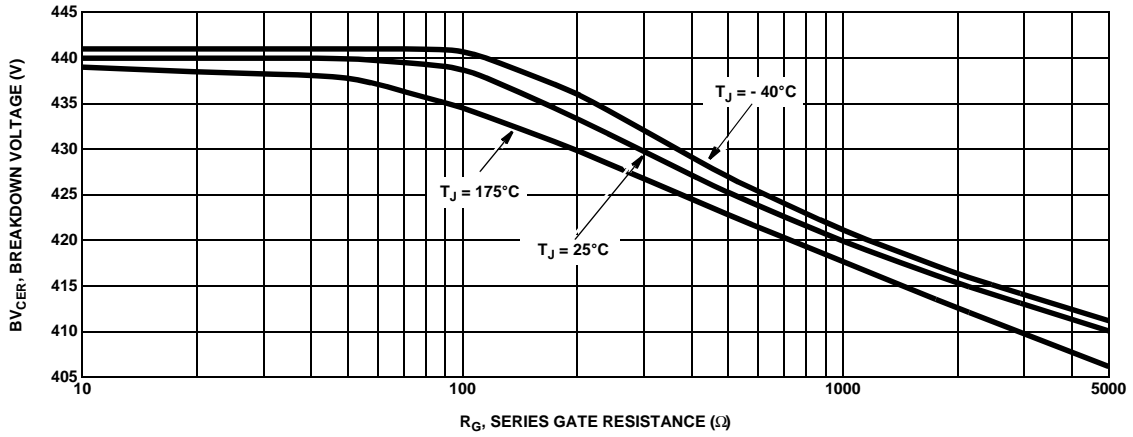


Figure 15. Breakdown Voltage vs Series Gate Resistance

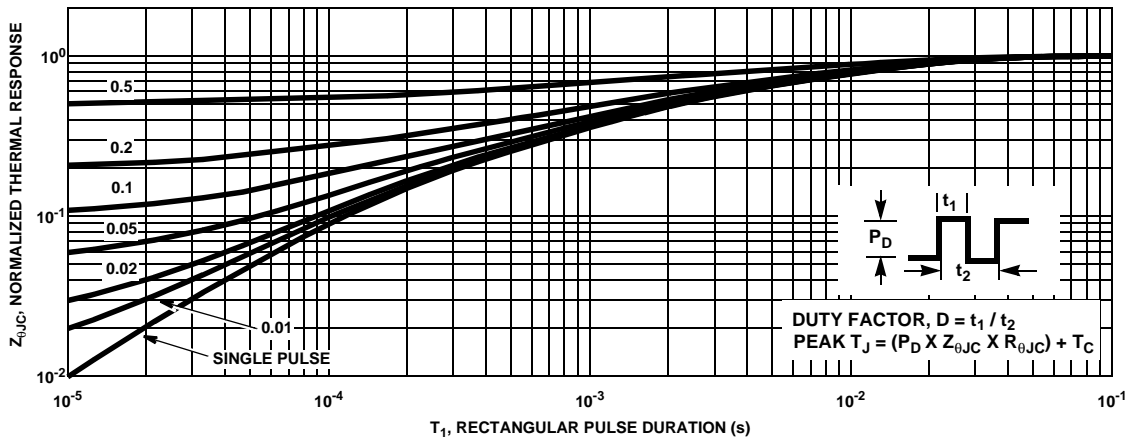


Figure 16. IGBT Normalized Transient Thermal Impedance, Junction to Case

Test Circuit and Waveforms

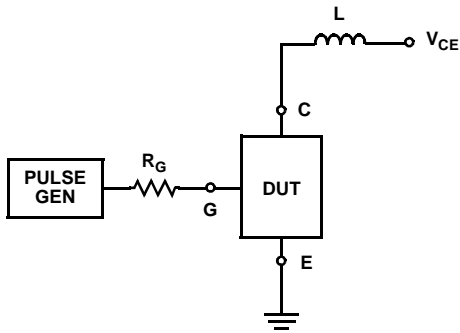


Figure 17. Inductive Switching Test Circuit

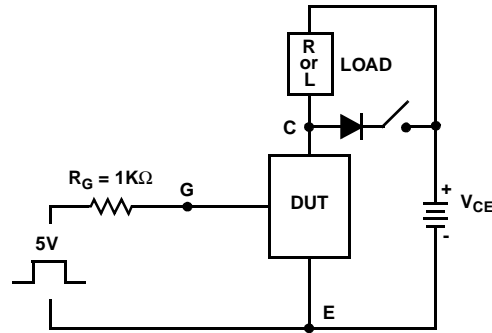


Figure 18. t_{ON} and t_{OFF} Switching Test Circuit

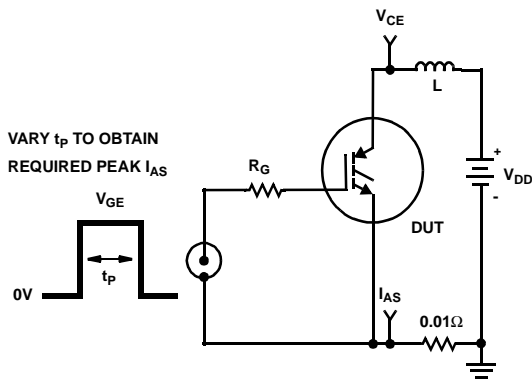


Figure 19. Unclamped Energy Test Circuit

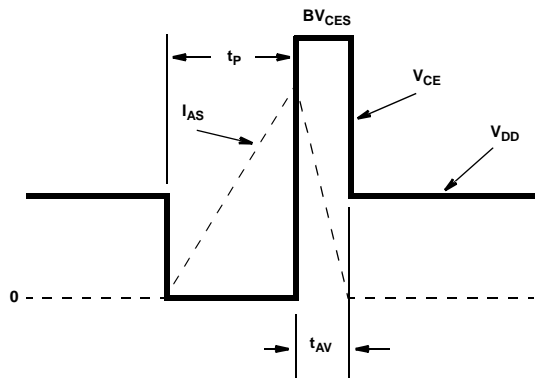


Figure 20. Unclamped Energy Waveforms

SPICE Thermal Model

```

REV 16 May 2005
ISL9V2540S3S
CTHERM1 th 6 19e -4
CTHERM2 6 5 12e -3
CTHERM3 5 4 15e -3
CTHERM4 4 3 25e -3
CTHERM5 3 2 69e -3
CTHERM6 2 tl 100e -3

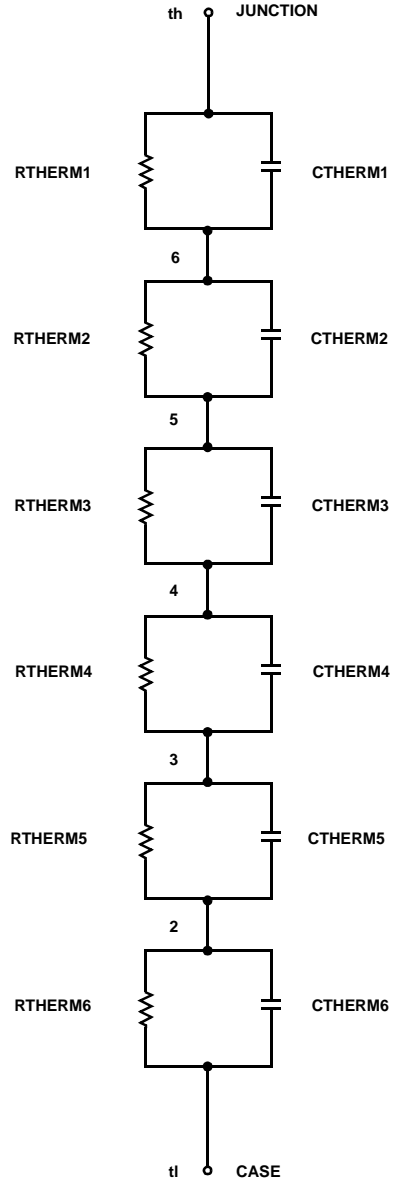
R THERM1 th 6 80e -3
R THERM2 6 5 81e -3
R THERM3 5 4 82e -3
R THERM4 4 3 100e -3
R THERM5 3 2 150e -3
R THERM6 2 tl 1645e -4
    
```

SABER Thermal Model

```

ISL9V2540S3S
template thermal_model th tl
thermal_c th, tl
{
    ctherm.ctherm1 th 6 = 19e -4
    ctherm.ctherm2 6 5 = 12e -3
    ctherm.ctherm3 5 4 = 15e -3
    ctherm.ctherm4 4 3 = 25e -3
    ctherm.ctherm5 3 2 = 69e -3
    ctherm.ctherm6 2 tl = 100e -3

    rtherm.rtherm1 th 6 = 80e -3
    rtherm.rtherm2 6 5 = 81e -3
    rtherm.rtherm3 5 4 = 82e -3
    rtherm.rtherm4 4 3 = 100e -3
    rtherm.rtherm5 3 2 = 150e -3
    rtherm.rtherm6 2 tl = 1645e -4
}
    
```



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| ActiveArray™ | FASTr™ | LittleFET™ | PowerTrench® | SyncFET™ |
| Bottomless™ | FPST™ | MICROCOUPLER™ | QFET® | TinyLogic® |
| Build it Now™ | FRFET™ | MicroFET™ | QS™ | TINYOPTO™ |
| CoolFET™ | GlobalOptoisolator™ | MicroPak™ | QT Optoelectronics™ | TruTranslation™ |
| CROSSVOLT™ | GTO™ | MICROWIRE™ | Quiet Series™ | UHC™ |
| DOME™ | HiSeC™ | MSX™ | RapidConfigure™ | UltraFET® |
| EcoSPARK™ | I ² C™ | MSXPro™ | RapidConnect™ | UniFET™ |
| E ² C MOS™ | i-Lo™ | OCX™ | μSerDes™ | VCX™ |
| EnSigna™ | ImpliedDisconnect™ | OCXPro™ | SILENT SWITCHER® | Wire™ |
| FACT™ | IntelliMAX™ | OPTOLOGIC® | SMART START™ | |
| FACT Quiet Series™ | | OPTOPLANAR™ | SPM™ | |
| Across the board. Around the world.™ | | PACMAN™ | Stealth™ | |
| The Power Franchise® | | POP™ | SuperFET™ | |
| Programmable Active Droop™ | | Power247™ | SuperSOT™-3 | |
| | | PowerEdge™ | SuperSOT™-6 | |

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|--------------------------|------------------------|---|
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